

INFORMATION DISCLOSURE

STATEMENT BY APPLICANT

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Complete if Known

Application Number	10/760,028
Filing Date	January 16, 2004
First Named Inventor:	Robert Chau, et al.
Art Unit	2891
Examiner Name	Smith, Bradley
Attorney Docket No.:	42P17814

Sheet 1 of 4

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)				
JRS ↓		US-	2003/0122186 A1	07-03-2003	Sekigawa et al.	
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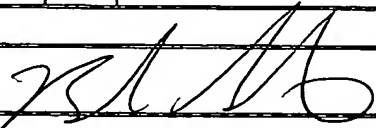
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 Sheet **2** of **4**

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		Number-Kind Code ² (If known)					
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		First Named Inventor:	Robert Chau, et al.	
		Art Unit	2891	
		Examiner Name	Smith, Bradley	
Sheet	3	of	Attorney Docket No.:	42P17814

FOREIGN PATENT DOCUMENTS							
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		Country Code ³	Number ⁴ Kind Code ⁵ (if known)				
TSKS		WO	2004/059726 A1	07-15-2004	IBM Corporation		
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Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
TSKS		International Search Report PCT/US2005/033439, mailed 1/31/2006 (7 pgs.)	
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JCS		T. M. MAYER, et al., "Chemical Vapor Deposition of Fluoroalkylsilane Monolayer Films for Adhesion Control in Microelectromechanical Systems" 2000 American Vacuum Society B 18(5), Sep/Oct 2000, pp. 2433-2440	
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<div style="display: flex; align-items: center; justify-content: center;"> <div style="margin-left: 20px;"> <p style="font-size: 1.2em; margin: 0;">INFORMATION DISCLOSURE STATEMENT BY APPLICANT</p> <p style="font-size: 0.8em; margin: 0;">(use as many sheets as necessary)</p> </div> </div>				Application Number	10/760,028
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		EP	1 202 335	A2	05/02/2002	IBM Corporation		
		EP	1 566 422	A2	08/24/2005	Samsung Electronics		

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		T. Park et al., "Fabrication of Body-Tied FinFETs (Omega MOSFETS) Using Bulk Si Wafers", 2003 Symposia on VLSI Technology Digest of Technical Papers, June 2003, pages 135-136.			
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